



SEMICONDUCTOR

DATA SHEET

BC846BPDW/BC847BPDW

Dual General Purpose Transistors**NPN/PNP Duals (Complimentary)**

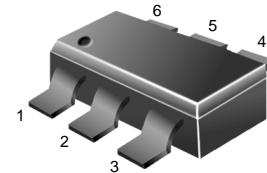
These transistors are designed for general purpose amplifier applications. They are housed in the SOT-363/SC-88 which is designed for low power surface mount applications.

Features

- Pb-Free Package is Available

MAXIMUM RATINGS – NPN

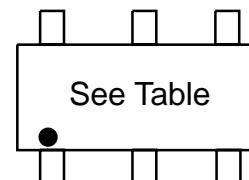
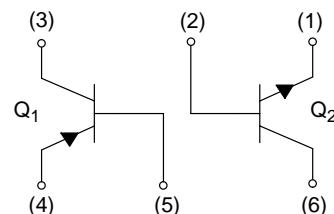
Rating	Symbol	Value	Unit
Collector-Emitter Voltage BC846 BC847 BC848	V_{CEO}	65 45 30	V
Collector-Base Voltage BC846 BC847 BC848	V_{CBO}	80 50 30	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current – Continuous	I_C	100	mAdc



SOT-363/SC-88
CASE 419B STYLE 1

MAXIMUM RATINGS – PNP

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BC846 BC847 BC848	V_{CEO}	-65 -45 -30	V
Collector-Base Voltage BC846 BC847 BC848	V_{CBO}	-80 -50 -30	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current – Continuous	I_C	-100	mAdc

**THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Total Device Dissipation Per Device FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	380 250 3.0	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	328	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-5 = 1.0 x 0.75 x 0.062 in.

ELECTRICAL CHARACTERISTICS

BC846BPDW/BC847BPDW

ELECTRICAL CHARACTERISTICS (NPN) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ($I_C = 10 \text{ mA}$)	$V_{(\text{BR})\text{CEO}}$	65 45 30	— — —	— — —	V
Collector–Emitter Breakdown Voltage ($I_C = 10 \mu\text{A}$, $V_{EB} = 0$)	$V_{(\text{BR})\text{CES}}$	80 50 30	— — —	— — —	V
Collector–Base Breakdown Voltage ($I_C = 10 \mu\text{A}$)	$V_{(\text{BR})\text{CBO}}$	80 50 30	— — —	— — —	V
Emitter–Base Breakdown Voltage ($I_E = 1.0 \mu\text{A}$)	$V_{(\text{BR})\text{EBO}}$	6.0 6.0 5.0	— — —	— — —	V
Collector Cutoff Current ($V_{CB} = 30 \text{ V}$) ($V_{CB} = 30 \text{ V}$, $T_A = 150^\circ\text{C}$)	I_{CBO}	— —	— —	15 5.0	nA μA
ON CHARACTERISTICS					
DC Current Gain ($I_C = 10 \mu\text{A}$, $V_{CE} = 5.0 \text{ V}$)	h_{FE}	— —	150 270	— —	—
($I_C = 2.0 \text{ mA}$, $V_{CE} = 5.0 \text{ V}$)		200 420	290 520	475 800	
Collector–Emitter Saturation Voltage ($I_C = 10 \text{ mA}$, $I_B = 0.5 \text{ mA}$) ($I_C = 100 \text{ mA}$, $I_B = 5.0 \text{ mA}$)	$V_{CE(\text{sat})}$	— —	— —	0.25 0.6	V
Base–Emitter Saturation Voltage ($I_C = 10 \text{ mA}$, $I_B = 0.5 \text{ mA}$) ($I_C = 100 \text{ mA}$, $I_B = 5.0 \text{ mA}$)	$V_{BE(\text{sat})}$	— —	0.7 0.9	— —	V
Base–Emitter Voltage ($I_C = 2.0 \text{ mA}$, $V_{CE} = 5.0 \text{ V}$) ($I_C = 10 \text{ mA}$, $V_{CE} = 5.0 \text{ V}$)	$V_{BE(\text{on})}$	580 —	660 —	700 770	mV
SMALL-SIGNAL CHARACTERISTICS					
Current–Gain – Bandwidth Product ($I_C = 10 \text{ mA}$, $V_{CE} = 5.0 \text{ Vdc}$, $f = 100 \text{ MHz}$)	f_T	100	—	—	MHz
Output Capacitance ($V_{CB} = 10 \text{ V}$, $f = 1.0 \text{ MHz}$)	C_{obo}	—	—	4.5	pF
Noise Figure ($I_C = 0.2 \text{ mA}$, $V_{CE} = 5.0 \text{ Vdc}$, $R_S = 2.0 \text{ k}\Omega$, $f = 1.0 \text{ kHz}$, $BW = 200 \text{ Hz}$)	NF	—	—	10	dB

ELECTRICAL CHARACTERISTICS

BC846BPDW/BC847BPDW

ELECTRICAL CHARACTERISTICS (PNP) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ($I_C = -10 \text{ mA}$)	$V_{(\text{BR})\text{CEO}}$	-65 -45 -30	— — —	— — —	V
Collector–Emitter Breakdown Voltage ($I_C = -10 \mu\text{A}, V_{EB} = 0$)	$V_{(\text{BR})\text{CES}}$	-80 -50 -30	— — —	— — —	V
Collector–Base Breakdown Voltage ($I_C = -10 \mu\text{A}$)	$V_{(\text{BR})\text{CBO}}$	-80 -50 -30	— — —	— — —	V
Emitter–Base Breakdown Voltage ($I_E = -1.0 \mu\text{A}$)	$V_{(\text{BR})\text{EBO}}$	-5.0 -5.0 -5.0	— — —	— — —	V
Collector Cutoff Current ($V_{CB} = -30 \text{ V}$) ($V_{CB} = -30 \text{ V}, T_A = 150^\circ\text{C}$)	I_{CBO}	— —	— —	-15 -4.0	nA μA

ON CHARACTERISTICS

DC Current Gain ($I_C = -10 \mu\text{A}, V_{CE} = -5.0 \text{ V}$)	BC846B, BC847B BC847C, BC848C	h_{FE}	— —	150 270	— —	—
($I_C = -2.0 \text{ mA}, V_{CE} = -5.0 \text{ V}$)	BC846B, BC847B BC847C, BC848C		200 420	290 520	475 800	
Collector–Emitter Saturation Voltage ($I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA}$) ($I_C = -100 \text{ mA}, I_B = -5.0 \text{ mA}$)		$V_{CE(\text{sat})}$	— —	— —	-0.3 -0.65	V
Base–Emitter Saturation Voltage ($I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA}$) ($I_C = -100 \text{ mA}, I_B = -5.0 \text{ mA}$)		$V_{BE(\text{sat})}$	— —	-0.7 -0.9	— —	V
Base–Emitter On Voltage ($I_C = -2.0 \text{ mA}, V_{CE} = -5.0 \text{ V}$) ($I_C = -10 \text{ mA}, V_{CE} = -5.0 \text{ V}$)		$V_{BE(\text{on})}$	-0.6 —	— —	-0.75 -0.82	V

SMALL-SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product ($I_C = -10 \text{ mA}, V_{CE} = -5.0 \text{ Vdc}, f = 100 \text{ MHz}$)	f_T	100	—	—	MHz
Output Capacitance ($V_{CB} = -10 \text{ V}, f = 1.0 \text{ MHz}$)	C_{ob}	—	—	4.5	pF
Noise Figure ($I_C = -0.2 \text{ mA}, V_{CE} = -5.0 \text{ Vdc}, R_S = 2.0 \text{ k}\Omega$, $f = 1.0 \text{ kHz}, \text{BW} = 200 \text{ Hz}$)	NF	—	—	10	dB

DEVICE CHARACTERISTICS

BC846BPDW/BC847BPDW

TYPICAL NPN CHARACTERISTICS – BC846

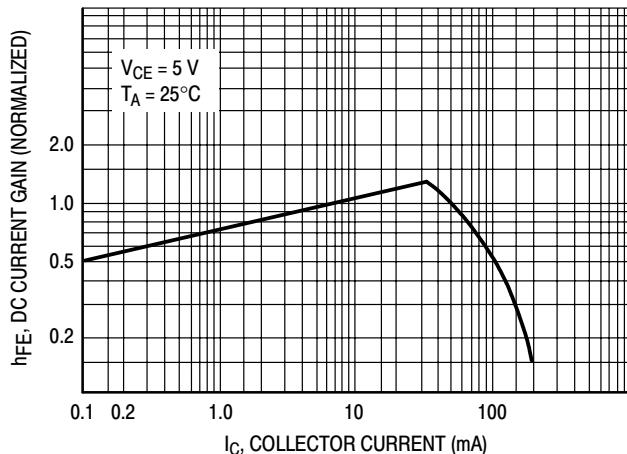


Figure 1. DC Current Gain

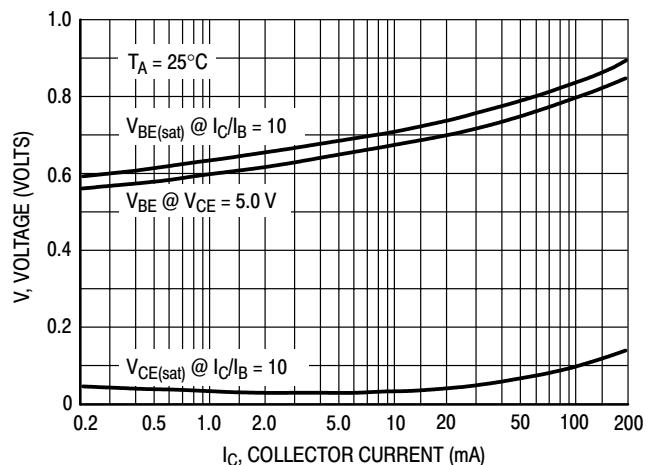


Figure 2. "On" Voltage

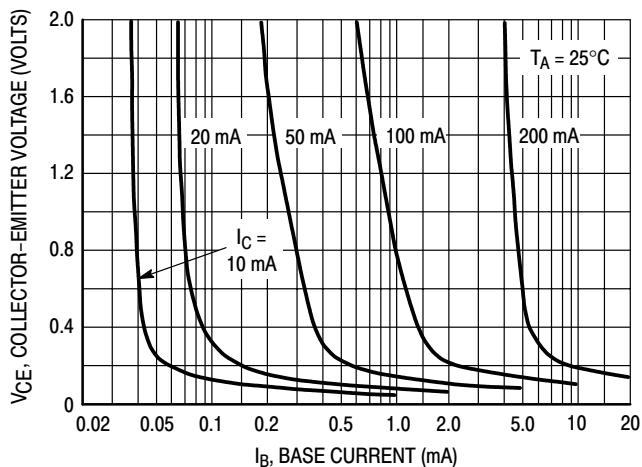


Figure 3. Collector Saturation Region

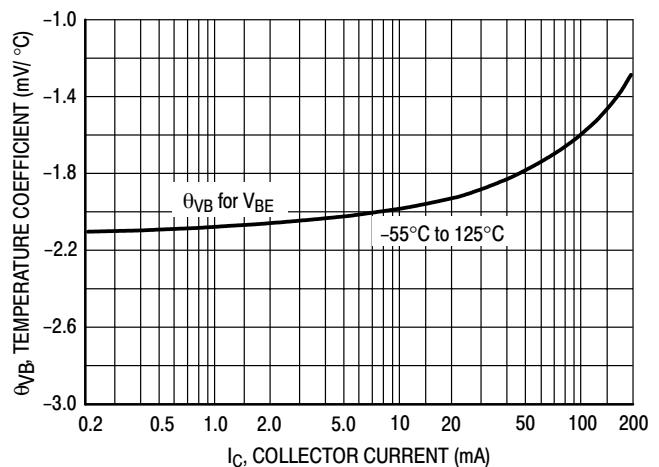


Figure 4. Base-Emitter Temperature Coefficient

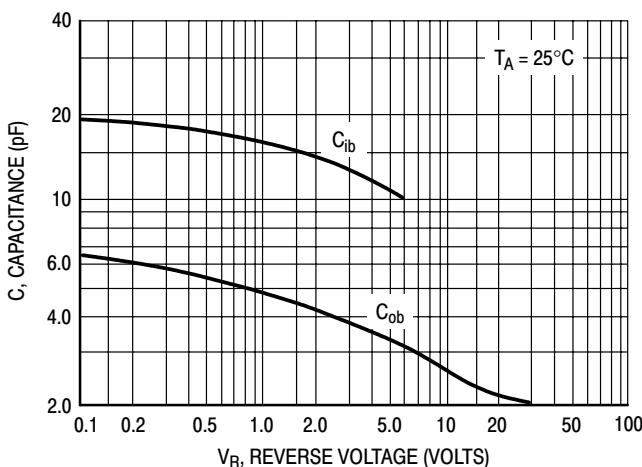


Figure 5. Capacitance

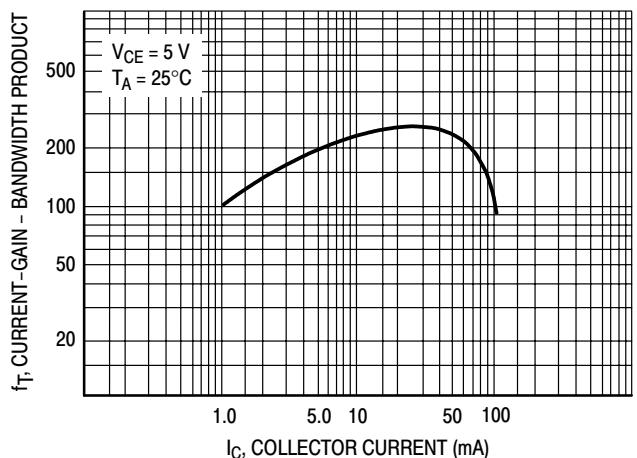


Figure 6. Current-Gain – Bandwidth Product

DEVICE CHARACTERISTICS

BC846BPDW/BC847BPDW

TYPICAL PNP CHARACTERISTICS — BC846

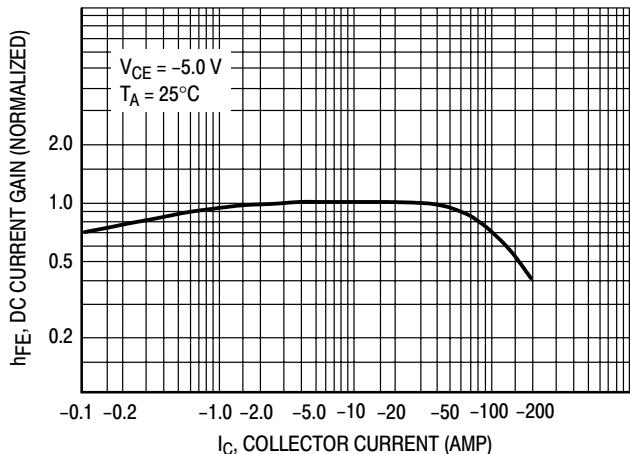


Figure 7. DC Current Gain

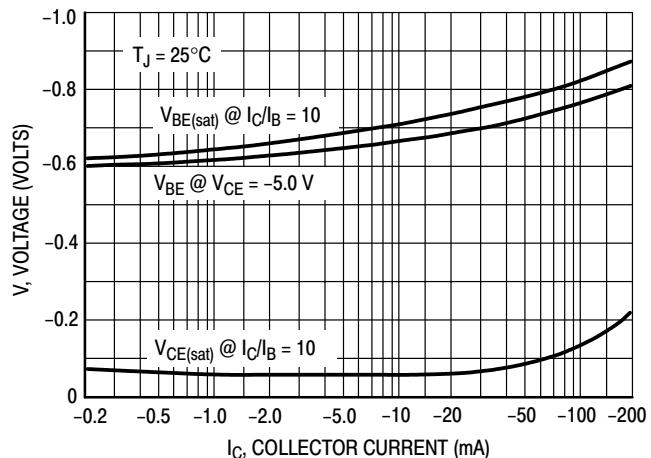


Figure 8. "On" Voltage

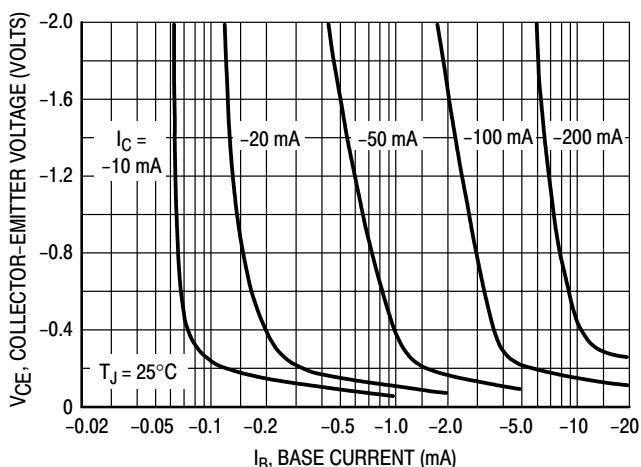


Figure 9. Collector Saturation Region

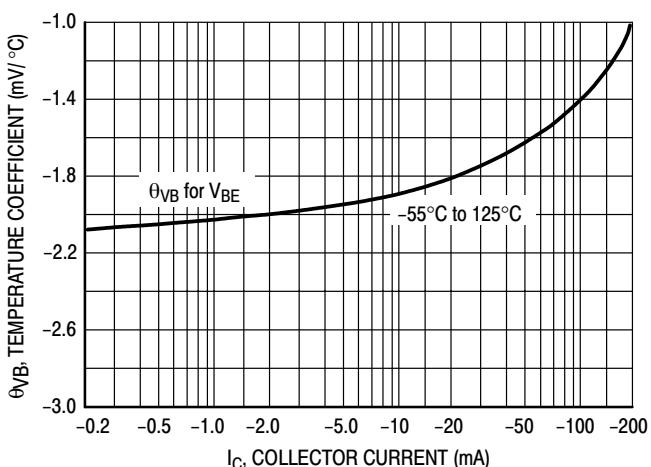


Figure 10. Base-Emitter Temperature Coefficient

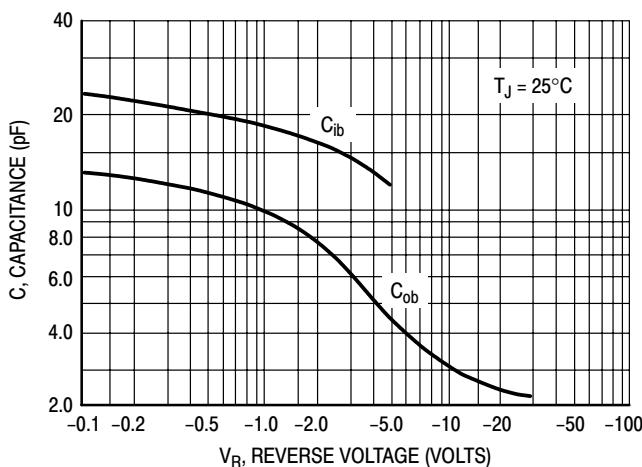


Figure 11. Capacitance

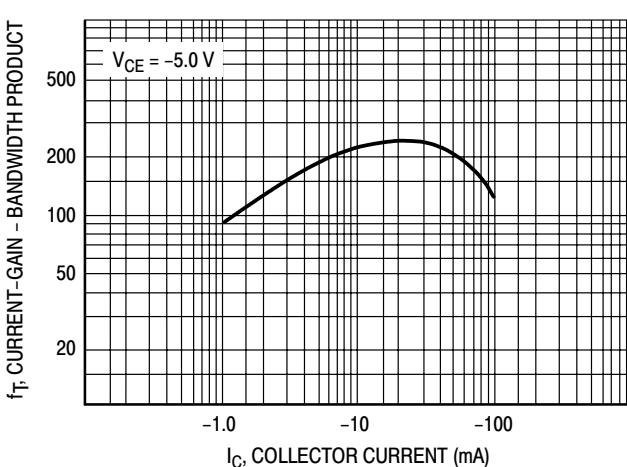


Figure 12. Current-Gain – Bandwidth Product

DEVICE CHARACTERISTICS

BC846BPDW/BC847BPDW

TYPICAL NPN CHARACTERISTICS – BC847 SERIES & BC848 SERIES

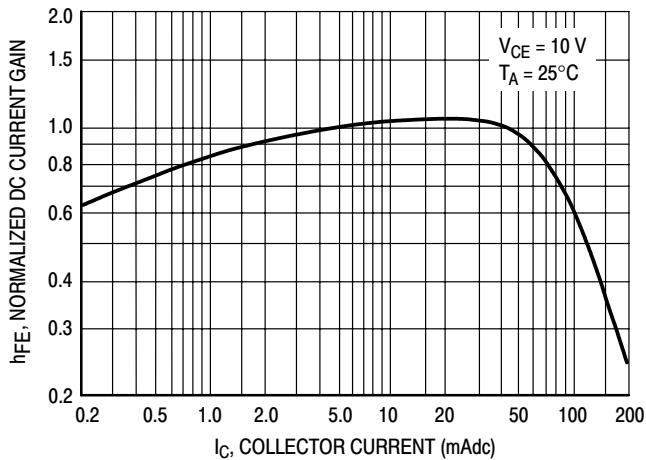


Figure 13. Normalized DC Current Gain

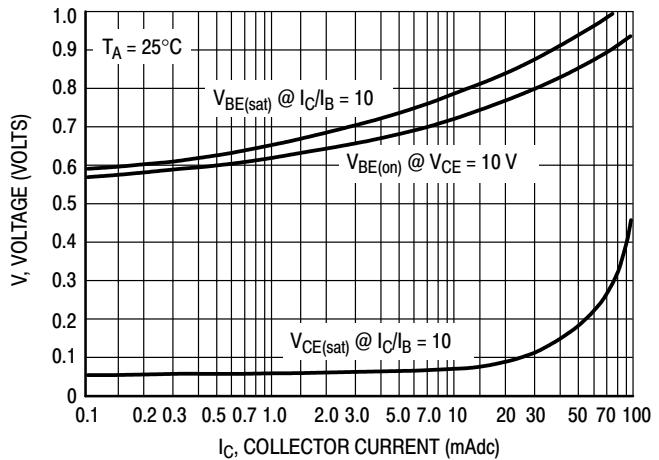


Figure 14. “Saturation” and “On” Voltages

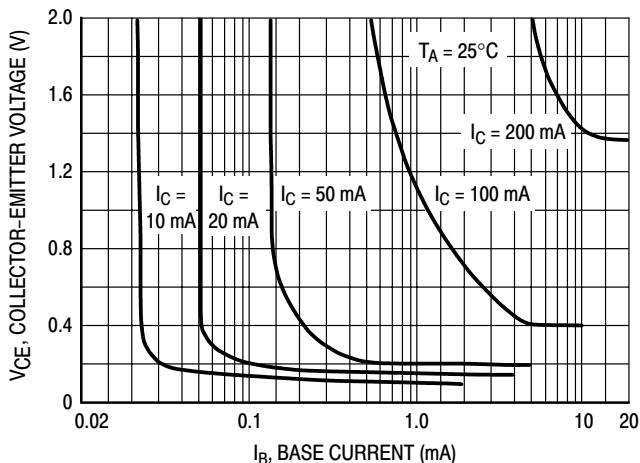


Figure 15. Collector Saturation Region

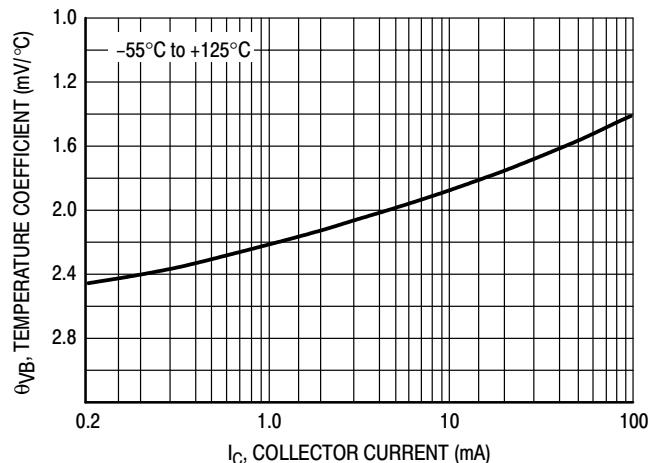


Figure 16. Base–Emitter Temperature Coefficient

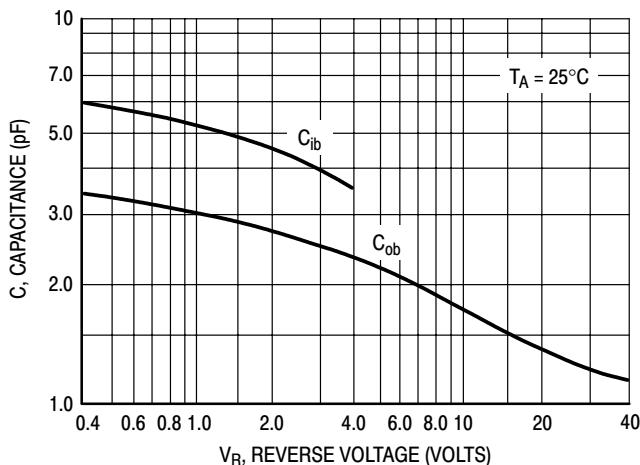


Figure 17. Capacitances

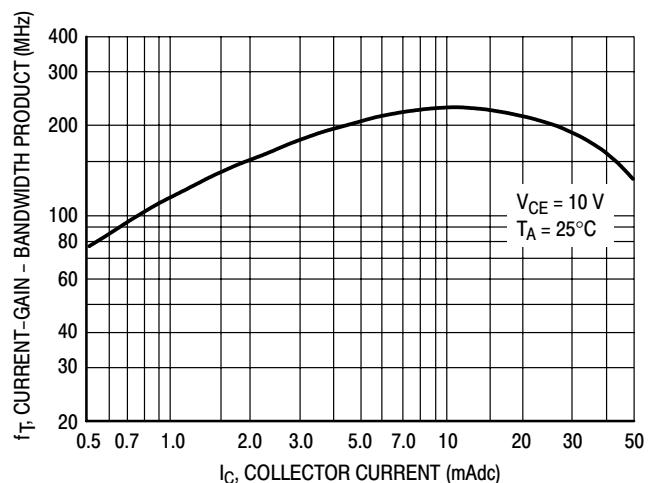


Figure 18. Current–Gain – Bandwidth Product

DEVICE CHARACTERISTICS

BC846BPDW/BC847BPDW

TYPICAL PNP CHARACTERISTICS — BC847 SERIES & BC848 SERIES

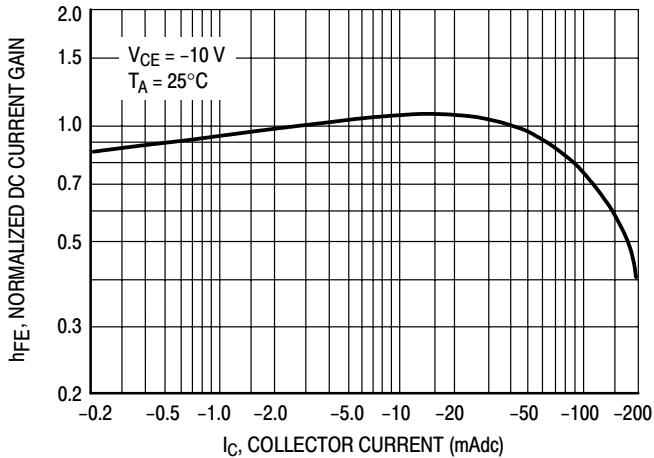


Figure 19. Normalized DC Current Gain

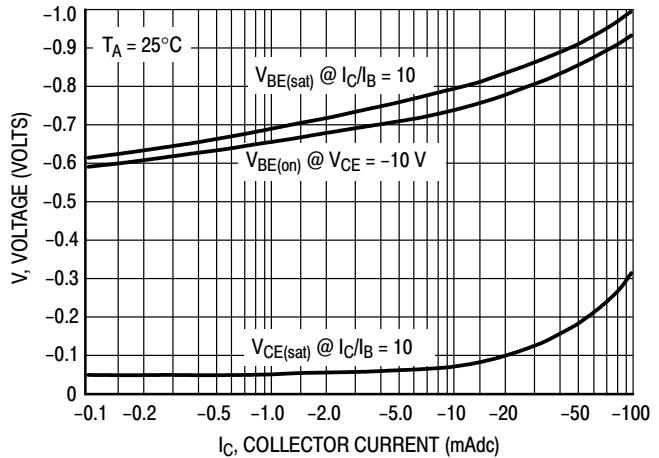


Figure 20. “Saturation” and “On” Voltages

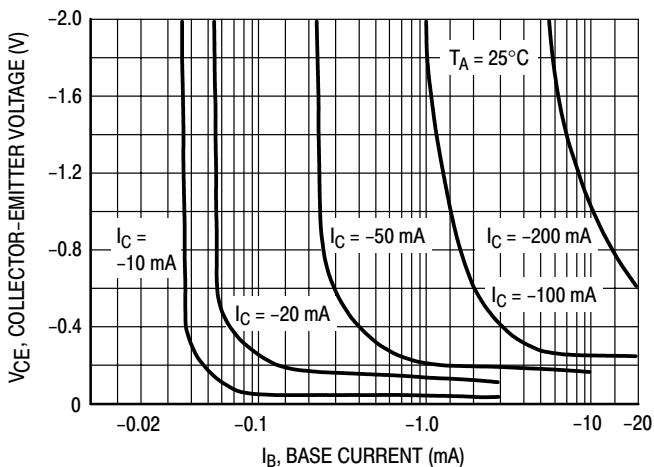


Figure 21. Collector Saturation Region

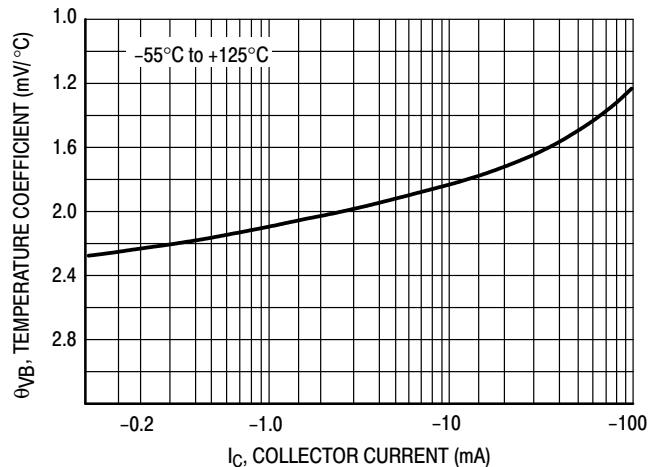


Figure 22. Base-Emitter Temperature Coefficient

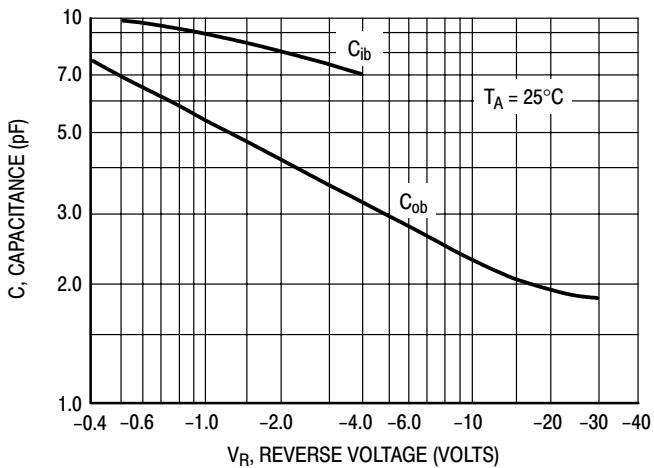


Figure 23. Capacitances

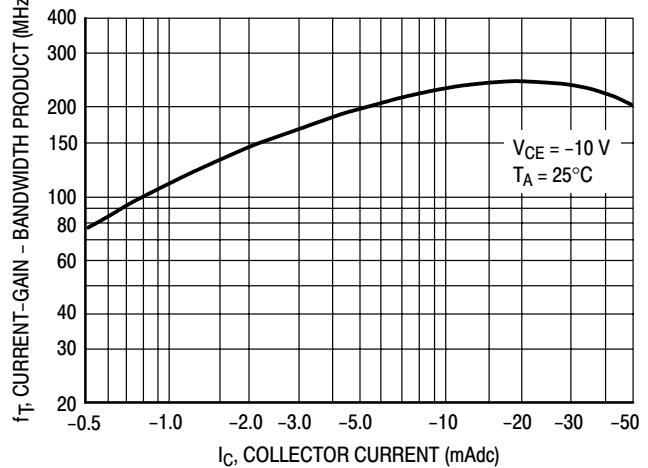


Figure 24. Current-Gain – Bandwidth Product

DEVICE CHARACTERISTICS

BC846BPDW/BC847BPDW

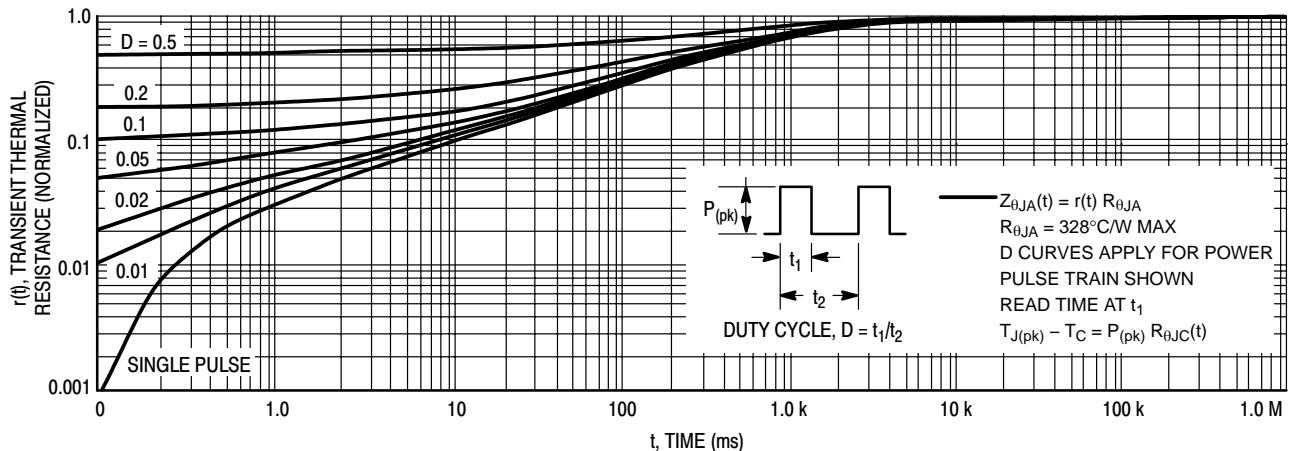


Figure 25. Thermal Response

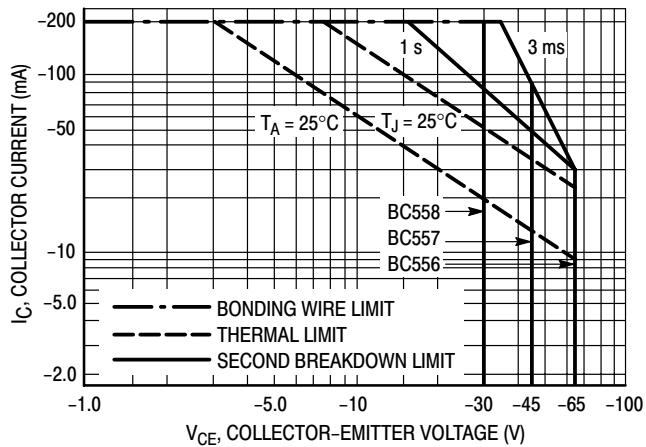


Figure 26. Active Region Safe Operating Area

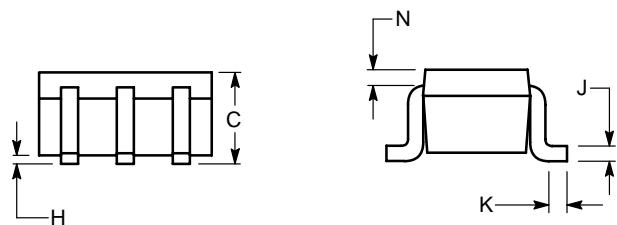
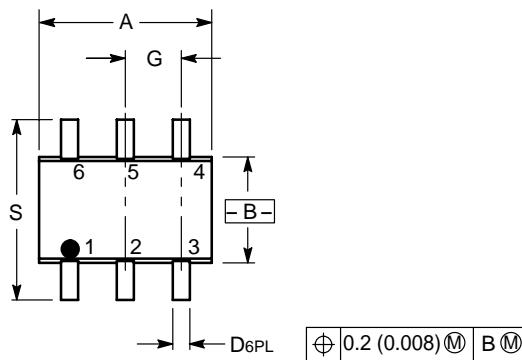
The safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 26 is based upon $T_{J(pk)} = 150^\circ\text{C}$; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 25. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

PACKAGE OUTLINE & DIMENSIONS

BC846BPDW/BC847BPDW

SC-88/SOT-363



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

- PIN 1. Emitter 1
 2. Base 1
 3. Collector 2
 4. Emitter 2
 5. Base 2
 6. Collector 1

